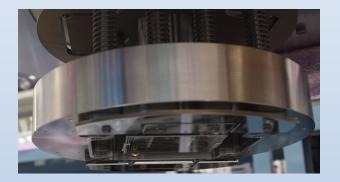
Sharing innovation moments with vacuum technology & glove box technology

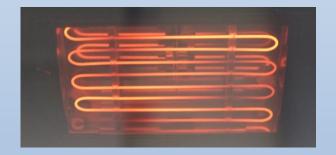
General purpose high temperature heating mechanism

It is possible to control substrate high temperature heating during film formation by installing it in evaporation system, sputtering system, etc.

Useful for evaluation of crystallinity, arrangement, modification, etc.







Specifications

l item	Specification	Remarks
Heating temperature	~600°C	Temperature monitor value
Effective heating area	約40mm×40mm	
Heater material	Tungsten	With a quartz plate shield
Heater capacity	20V,20A	Approximately 10V-11A at 500°C
Temperature monitor	K type thermocouple	Type changeable
Usage environment	Vacuum (less than 7 × 10 ⁻² Pa)	

Option

~900°Cspecification / Various susceptors / Substrate trays / etc



Dimension

